

10.0 Amps, 800 Volts N-Channel MOS-FET

DESCRIPTION

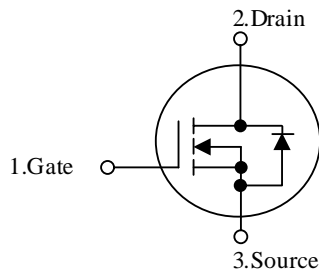
These N-Channel enhancement mode power field effect Transistors are produced using planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on - state resistance , provide superior switching performance, and Withstand high energy pulse in the avalanche and commutation mode .These devices are well suited for high efficiency switch mode power supply, electronic lamp ballasts based on half bridge topology.

FEATURES

- * $R_{DS(ON)} = 1.15\Omega @ V_{GS} = 10V$
- * Fast switching capability
- * Avalanche energy tested
- * Improved dv/dt capability, high ruggedness

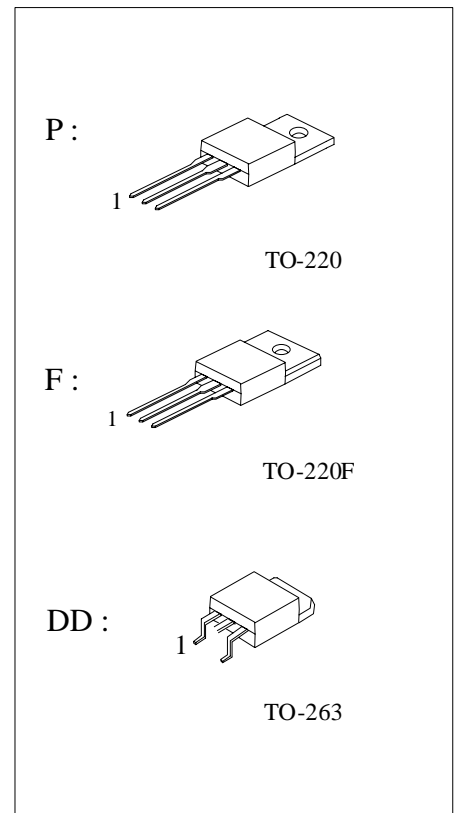
SYMBOL



ORDERING INFORMATION

Order Number	Package	Pin Assignment			Packing
		1	2	3	
FTK10N80P	TO-220	G	D	S	Tube
FTK10N80F	TO-220F	G	D	S	Tube
FTK10N80DD	TO-263	G	D	S	Reel & Taping

Note: Pin Assignmen: G: Gate D: Drain S: Source





FTK10N80P/F/DD

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, unless otherwise specified)

PARAMET		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	800	V
Gate-Source Voltage		V _{GSS}	±30	V
Avalanche Current (Note 1)		I _{AR}	10	A
Continuous Drain Current	T _C = 25°C	I _D	10	A
	T _C = 100°C		6.0	
Pulsed Drain Current (Note 1)		I _{DM}	36	A
Avalanche Energy	Single Pulse(Note 2)	E _{AS}	920	mJ
	Repetitive Limited by T _{J(MAX)}	E _{AR}	17	mJ
Peak Diode Recovery dv/dt (Note 3)		dv/dt	4.5	V/ns
Power Dissipation (TO-220,TO-263/ TO-220F)	T _C = 25°C	P _D	142 / 65	W
	Derate above 25°C		1.14 / 0.38	W / °C
Junction Temperature		T _J	+150	°C
Operating and Storage Temperature		T _{STG}	-55 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER		SYMBOL	MIN	TYP	MAX	UNIT
Junction-to-Ambient		θ _{JA}			62.5	°C / W
Junction-to-Case	TO-220, TO-263	θ _{Jc}			0.88	
	TO-220F	θ _{Jc}			1.93	

■ ELECTRICAL CHARACTERISTICS (T_C = 25°C, unless Otherwise specified.)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250μA	800			V	
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 800V, V _{GS} = 0V			10	μA	
Gate-Body Leakage Current	Forward	I _{GSSF}	V _{GS} = 30V, V _{DS} = 0V			100	nA	
	Reverse	I _{GSSR}	V _{GS} = -30V, V _{DS} = 0V			-100	nA	
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} / ΔT _J	I _D = 250μA, Referenced to 25°C		0.99		V / °C	
ON CHARACTERISTICS								
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V	
Static Drain-Source On-Resistance		R _{DS(ON)}	V _{GS} = 10V, I _D = 5.0A		0.92	1.15	Ω	
Forward Transconductance		g _{FS}	V _{DS} = 40V, I _D = 3.5A (Note 4)		5.5		S	
DYNAMIC CHARACTERISTICS								
Input Capacitance		C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz		2800		pF	
Output Capacitance		C _{OSS}				230		pF
Reverse Transfer Capacitance		C _{RSS}				20		pF
SWITCHING CHARACTERISTICS								
Turn-On Delay Time		t _{D(ON)}	V _{DD} = 400V, I _D = 9.4A, R _G = 25Ω (Note 4,5)		60		ns	
Turn-On Rise Time		t _r				150		ns
Turn-Off Delay Time		t _{D(OFF)}				120		ns
Turn-Off Fall Time		t _f				120		ns
Total Gate Charge		Q _G	V _{DS} = 640V, I _D = 9.4A, V _{GS} = 10V (Note 4,5)		58		nC	
Gate-Source Charge		Q _{GS}				17.5		nC
Gate-Drain Charge		Q _{GD}				22		nC



FTK10N80P/F/DD

■ ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$, unless Otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS						
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 10\text{ A}$			1.4	V
Maximum Continuous Drain-Source Diode Forward Current	I_S				10	A
Maximum Pulsed Drain-Source Diode Forward Current	I_{SM}				36	A
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, I_S = 10\text{ A},$		650		ns
Reverse Recovery Charge	Q_{RR}	$dI_F/dt = 100\text{ A}/\mu\text{s}$ (Note 4)		7.0		μC

Note:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 17.3\text{ mH}, I_{AS} = 10\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 9.4\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test: Pulse width $\leq 300\ \mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

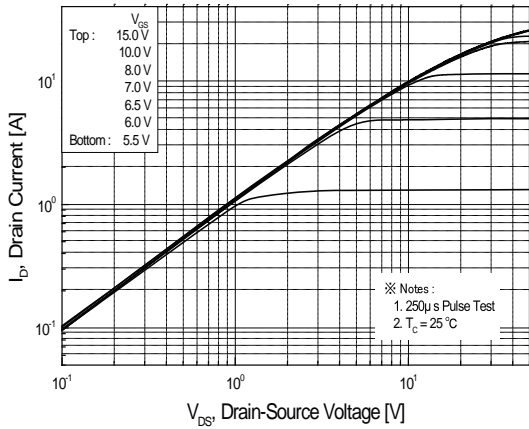


Figure 1. On Region Characteristics

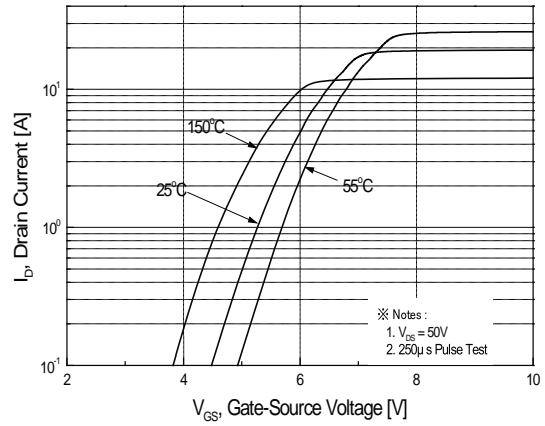


Figure 2. Transfer Characteristics

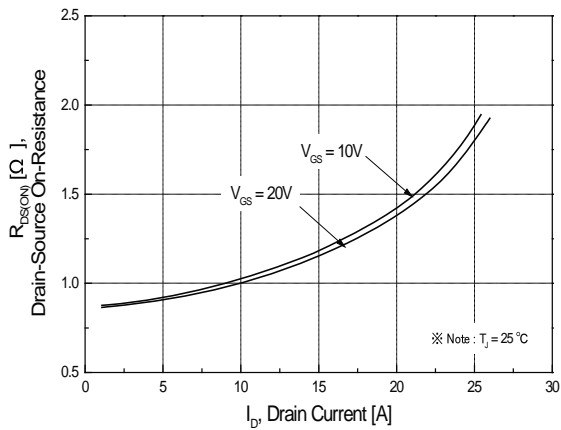


Figure 3. On Resistance Variation vs Drain Current and Gate Voltage

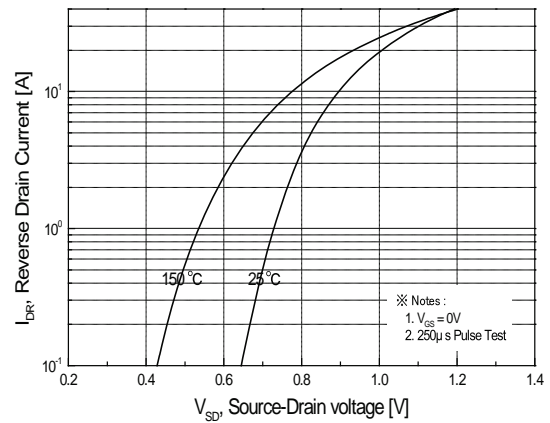


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

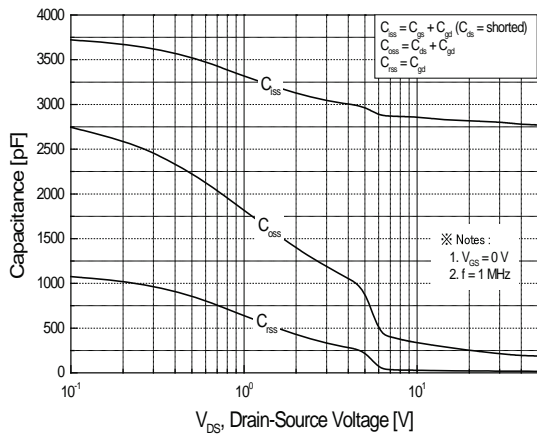


Figure 5. Capacitance Characteristics

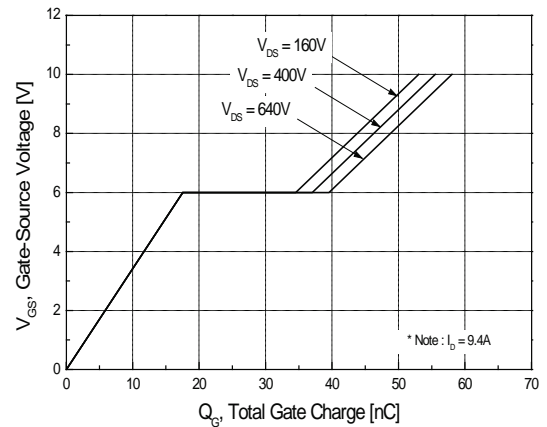


Figure 6. Gate Charge Characteristics

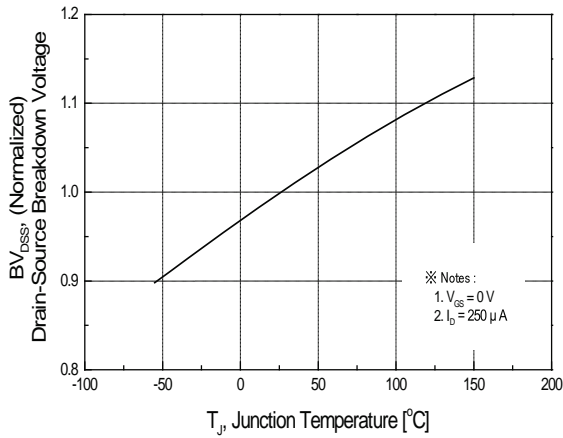


Figure 7. Breakdown Voltage Variation vs Temperature

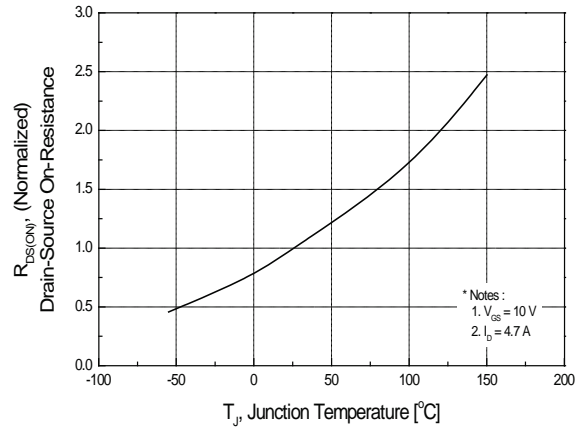


Figure 8. On-Resistance Variation vs Temperature

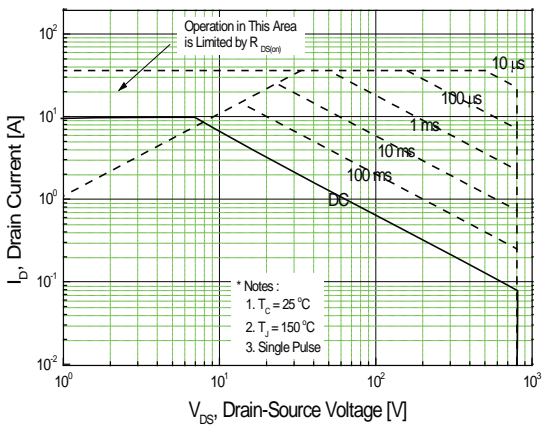


Figure 9. Maximum Safe Operating Area

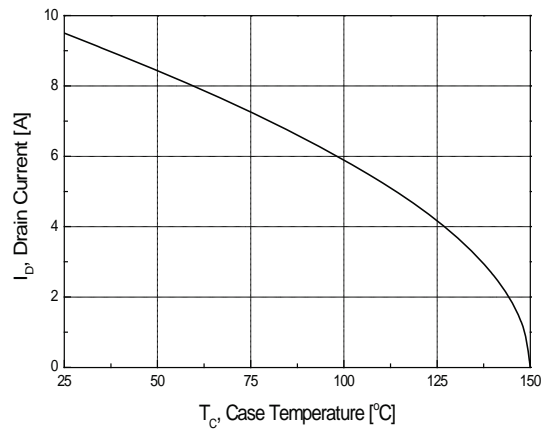


Figure 10. Maximum Drain Current vs Case Temperature

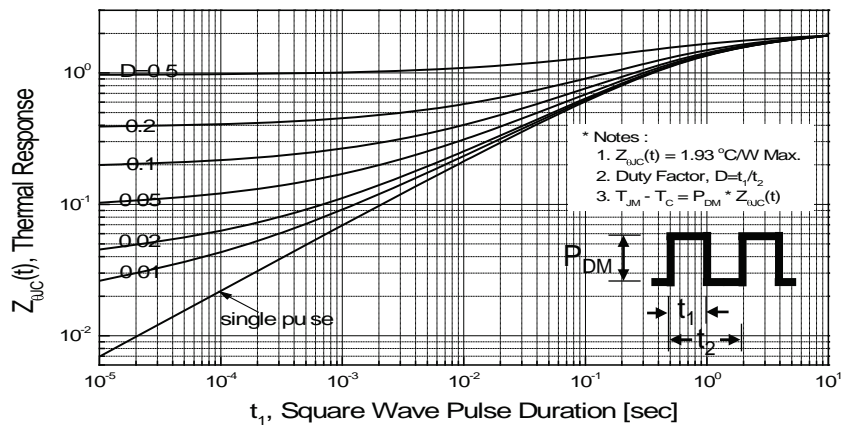


Figure 11. Transient Thermal Response Curve

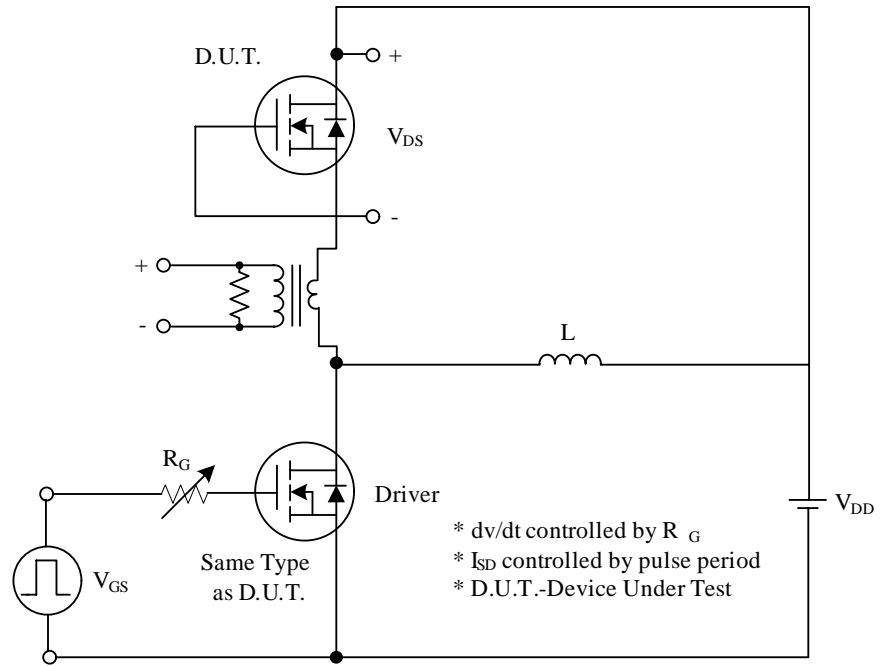


Fig. 1A Peak Diode Recovery dv/dt Test Circuit

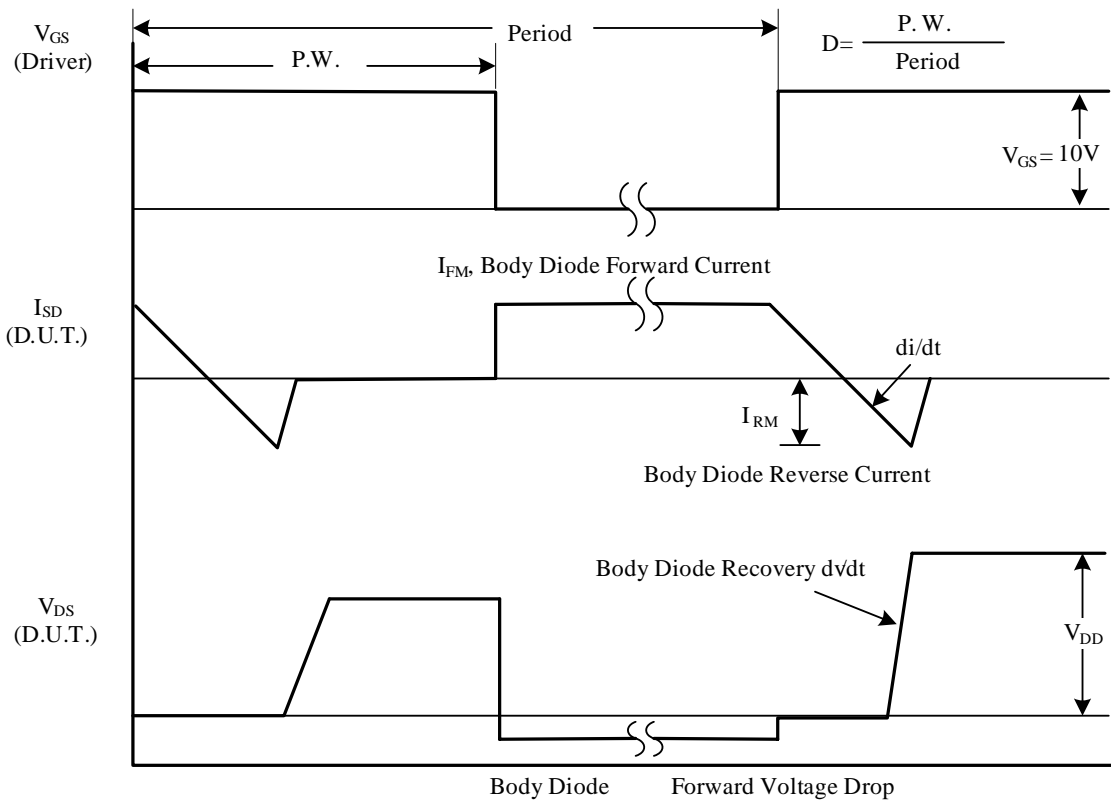


Fig. 1B Peak Diode Recovery dv/dt Waveforms

■ TEST CIRCUITS AND WAVEFORMS (Cont.)

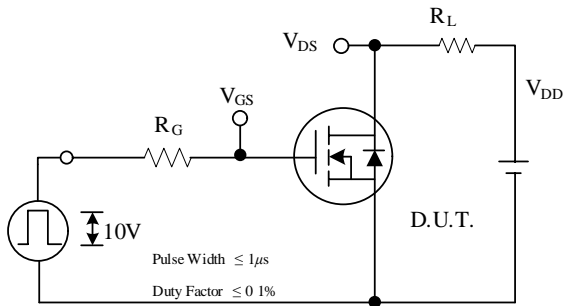


Fig. 2A Switching Test Circuit

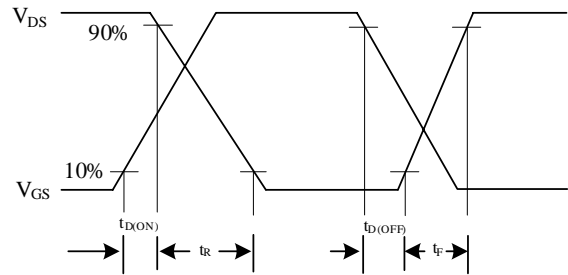


Fig. 2B Switching Waveforms

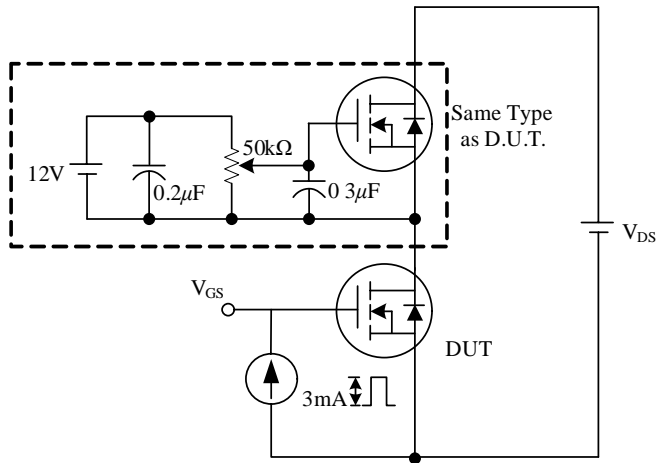


Fig. 3A Gate Charge Test Circuit

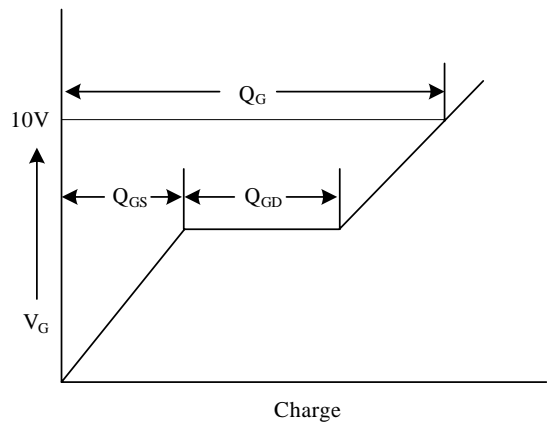


Fig. 3B Gate Charge Waveform

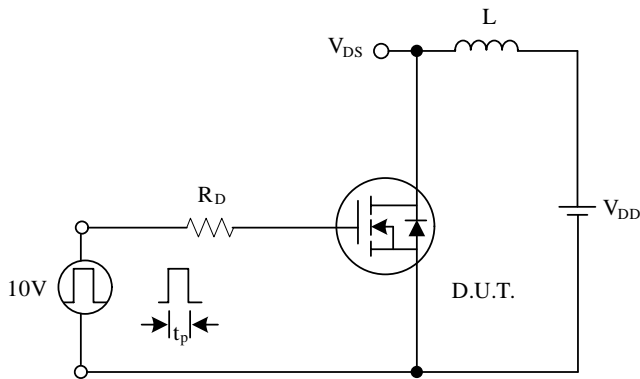


Fig. 4A Unclamped Inductive Switching Test Circuit

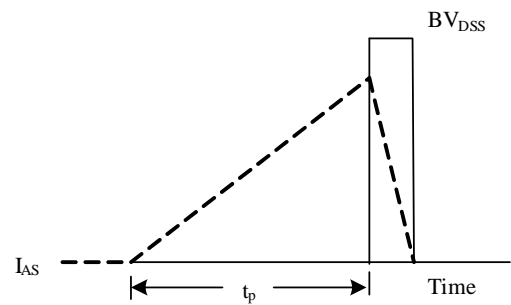


Fig. 4B Unclamped Inductive Switching Waveforms